

# Dianyu Qi

## List of Publications by Year in descending order

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Version: 2024-02-01

14  
papers

423  
citations

933447

10  
h-index

1125743

13  
g-index

14  
all docs

14  
docs citations

14  
times ranked

825  
citing authors

#	ARTICLE	IF	CITATIONS
1	Surface Functionalization of Black Phosphorus via Potassium toward High-Performance Complementary Devices. <i>Nano Letters</i> , 2017, 17, 4122-4129.	9.1	117
2	Strong Interlayer Transition in Few-Layer InSe/PdSe <sub>2</sub> van der Waals Heterostructure for Near-Infrared Photodetection. <i>Advanced Functional Materials</i> , 2021, 31, 2104143.	14.9	69
3	Fabry-Perot Cavity-Enhanced Optical Absorption in Ultrasensitive Tunable Photodiodes Based on Hybrid 2D Materials. <i>Nano Letters</i> , 2017, 17, 7593-7598.	9.1	48
4	Continuously Tuning Electronic Properties of Few-Layer Molybdenum Ditelluride with <i>in Situ</i> Aluminum Modification toward Ultrahigh Gain Complementary Inverters. <i>ACS Nano</i> , 2019, 13, 9464-9472.	14.6	36
5	Reducing the Schottky barrier between few-layer MoTe <sub>2</sub> and gold. <i>2D Materials</i> , 2017, 4, 045016.	4.4	35
6	Ultrathin Single-Crystalline 2D Perovskite Photoconductor for High-Performance Narrowband and Wide Linear Dynamic Range Photodetection. <i>Small</i> , 2020, 16, e2005626.	10.0	26
7	Molecular Alignment and Electronic Structure of <i>N,N</i> -Dibutyl-3,4,9,10-perylene-tetracarboxylic-diimide Molecules on MoS <sub>2</sub> Surfaces. <i>ACS Applied Materials &amp; Interfaces</i> , 2017, 9, 5566-5573.	8.0	19
8	Facile p-Doping of Few-Layer MoTe <sub>2</sub> by Controllable Surface Oxidation toward High-Performance Complementary Devices. <i>ACS Applied Electronic Materials</i> , 2020, 2, 920-926.	4.3	19
9	Flexible Photodetectors Based on All-Solution-Processed Cu Electrodes and InSe Nanoflakes with High Stabilities. <i>Advanced Functional Materials</i> , 2022, 32, 2108261.	14.9	18
10	Visible to near-infrared photodetector with novel optoelectronic performance based on graphene/S-doped InSe heterostructure on h-BN substrate. <i>Nanoscale</i> , 2020, 12, 19259-19266.	5.6	17
11	Modulation of Electrical Properties with Controllable Local Doping in Multilayer MoTe <sub>2</sub> Transistors. <i>Advanced Electronic Materials</i> , 2020, 6, 2000532.	5.1	10
12	Epitaxial Growth of 2D Ternary Copper-Indium-Selenide Nanoflakes for High-Performance Near-Infrared Photodetectors. <i>Advanced Optical Materials</i> , 0, , 2200033.	7.3	4
13	Bandgap Engineering of Ternary $\text{InSe}_{1-x}\text{S}_x$ and $\text{InSe}_{1-y}\text{Te}_y$ Single Crystals for High-Performance Electronics and Optoelectronics. <i>Advanced Optical Materials</i> , 2022, 10, .	7.3	3
14	Selective Chemical Vapor Deposition Growth of WS <sub>2</sub> /MoS <sub>2</sub> Vertical and Lateral Heterostructures on Gold Foils. <i>Nanomaterials</i> , 2022, 12, 1696.	4.1	2